

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/723,771	11/26/2003	Fu-Hsin Chen	TSM03-0586	9697	
43859 75	90 05/20/2005		EXAMINER		
SLATER & MATSIL, L.L.P. 17950 PRESTON ROAD, SUITE 1000			LINDSAY JR, WALTER LEE		
DALLAS, TX 75252			ART UNIT	PAPER NUMBER	
,			2812		
			DATE MAILED: 05/20/2009	DATE MAILED: 05/20/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)			
•••	10/723,771	CHEN ET AL.			
Office Action Summary	Examiner	Art Unit			
	Walter L. Lindsay, Jr.	2812			
The MAILING DATE of this communication apperiod for Reply	opears on the cover sheet with	the correspondence address			
A SHORTENED STATUTORY PERIOD FOR REP THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR 1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a re - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statu Any reply received by the Office later than three months after the mail earned patent term adjustment. See 37 CFR 1.704(b).		y be timely filed 30) days will be considered timely. IS from the mailing date of this communication. IDONED (35 U.S.C. § 133).			
Status					
1) Responsive to communication(s) filed on					
2a) ☐ This action is FINAL. 2b) ☑ Th	· · · · · · · · · · · · · · · · · · ·				
,—	Since this application is in condition for allowance except for formal matters, prosecution as to the ments is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.				
Disposition of Claims					
 4) Claim(s) 1-28 is/are pending in the application 4a) Of the above claim(s) 19-28 is/are withdrays 5) Claim(s) 15-18 is/are allowed. 6) Claim(s) 1,2 and 5-11 is/are rejected. 7) Claim(s) 3,4 and 12-14 is/are objected to. 8) Claim(s) are subject to restriction and/a 	awn from consideration.				
Application Papers					
9) The specification is objected to by the Examiner.					
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.					
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).					
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).					
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.					
Priority under 35 U.S.C. § 119					
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documer 2. Certified copies of the priority documer 3. Copies of the certified copies of the priority application from the International Bure. * See the attached detailed Office action for a list	nts have been received. nts have been received in Appointy documents have been re au (PCT Rule 17.2(a)).	olication No eceived in this National Stage			
Attachment(s)					
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08 Paper No(s)/Mail Date 3/22/2004. 		Mail Date rmal Patent Application (PTO-152)			

DETAILED ACTION

This Office Action is in response to an Election filed on 2/23/2005.

Currently, claims 1-28 are pending. Claims 19-28 have been withdrawn from consideration.

Election/Restrictions

- 1. Applicant's election without traverse of claims 1-18 in the reply filed on 2/23/2005 is acknowledged.
- 2. Claims 19-28 have been withdrawn from further consideration pursuant to 37 CFR 1.142(b) as being drawn to a nonelected device, there being no allowable generic or linking claim. Election was made **without** traverse in the reply filed on 2/23/2005.

Specification

3. The specification has not been checked to the extent necessary to determine the presence of all possible minor errors. Applicant's cooperation is requested in correcting any errors of which applicant may become aware in the specification.

Claim Rejections - 35 USC § 102

4. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 5. Claims 1,2 and 5-11 are rejected under 35 U.S.C. 102(b) as being anticipated by Chu (U.S. Patent No. 6,297,108 dated 10/2/2001).

Art Unit: 2812

Chu shows the method as claimed in Figs. 3 to 9 and corresponding text as: providing a substrate (60) comprising an isolation region (74) and an active region (col. 3, line 66-col. 4, line 6); forming a first doped region (73) in the active region of the substrate with a first plurality of ions (col. 3, lines 54-65); driving in the ions of the first doped region further into the substrate to enlarge the first doped region (75) and to make boundaries of the first doped region graded (col. 3, line 66-col. 4, line 6); forming a gate electrode (78) over the substrate after the driving in step, wherein at least part of the gate electrode is located in the active region, and wherein at least part of the gate electrode extends over a part of the first doped region (col. 4, lines 15-24); forming a spacer (80) along edges of the gate electrode to form an intermediate structure (col. 4, lines 25-36); and forming a second doped region (81) with a second plurality of ions within the first doped region, wherein a gate-side boundary of the second doped region is separated from a closest edge of the gate electrode by a first spaced distance, wherein the gate-side boundary of the second doped region is separated from a closest edge of the spacer by a second spaced distance, the second spaced distance being less than the first spaced distance (col. 4, lines 15-24) (distance not specified)(claim 1). Chu teaches forming a first mask layer (68) over the substrate, wherein the first patterned mask layer has a first opening (69) formed therein at a location in the active region, wherein the forming of the first doped region comprises implanting the first plurality of ions into the substrate at the first location through the first opening (col. 3, lines 40-53) (claim 2). Chu teaches that the driving in step is performed at a temperature between about 1000 and about 1200°C (col. 3, line 66-col. 4, line 6) (claim

Application/Control Number: 10/723,771 Page 4

Art Unit: 2812

5). Chu teaches that the isolation region has a field oxide structure (col. 3, line 66-col. 4, line 6) (claim 6). Chu teaches that the isolation region has a shallow trench filled with insulating material (col. 3, line 66-col. 4, line 6) (claim 7). Chu teaches that the removing of the first patterned mask layer occurs before the driving in step (col. 3, lines 44-65) (claim 8). Chu teaches that the removing of the first patterned mask layer occurs after the driving in step (col. 3, lines 44-65) (claim 9). Chu teaches that the removing of the first patterned mask layer occurs during the driving in step (col. 3, lines 44-65) (claim 10). Chu teaches that the first patterned mask layer comprises photoresist material (col. 3, lines 44-65) (claim 11).

Allowable Subject Matter

- 6. Claims 3, 4 and 12-14 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.
- 7. Claims 15-18 are allowed.
- 8. The following is a statement of reasons for the indication of allowable subject matter: the prior art, either singly or in combination fails to anticipate or render obvious, the limitations of:

...forming a second patterned mask layer over the intermediate structure, wherein the second patterned mask layer has a second opening formed therein at a second location in the active region, and wherein the second location is located within the first location, as required by claim 3, as it depends from claim 2, and as required by claim 15.

Art Unit: 2812

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Walter L. Lindsay, Jr. whose telephone number is (571) 272-1674. The examiner can normally be reached on Monday-Thursday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael S. Lebentritt can be reached on (571) 272-1873. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Walter L. Lindsay, Jr. Examiner Art Unit 2812

WLL Linds II. Walk L. Linds II. May 13, 2005